

SGM7229 High-Speed USB 2.0 (480Mbps) DPDT Analog Switch

GENERAL DESCRIPTION

The SGM7229 is a DPDT (double-pole/double-throw) analog switch. It operates from a 1.8V to 5.5V single power supply. Each switch of the SGM7229 is bidirectional, which can ensure that the high speed signals have little or no attenuation at the outputs.

The SGM7229 features high speed, low bit-to-bit skew and wide bandwidth. These high performances make it very suitable for multiple applications, such as cellular phones and computer peripherals, etc.

The SGM7229 has power-off and power-on protections. Because of the special circuitry on the D+/D- pins, the device will not be damaged even if V_{BUS} short-circuit occurs during data transmission. In addition, it can prevent accidental from leaking and ensure system reliability under power-down and over-voltage conditions.

The SGM7229 is available in Green MSOP-10 and UTQFN-1.8×1.4-10L packages. It operates over an ambient temperature range of -40°C to +85°C.

FEATURES

- Single Supply Voltage Range: 1.8V to 5.5V
- On-Resistance: 6Ω (TYP) at 3V
- High Off-Isolation: -26dB ($R_L = 50\Omega$, f = 250MHz)
- Low Crosstalk: -20dB ($R_L = 50\Omega$, f = 250MHz)
- -3dB Bandwidth: 850MHz
- Fast Switching Times at V_{cc} = 3.3V:

 $t_{ON} = 30$ ns $t_{OFF} = 18$ ns

- Break-Before-Make Switching
- Rail-to-Rail Input and Output Operation
- Power-Off and Power-On Protections
- -40°C to +85°C Operating Temperature Range
- Available in Green UTQFN-1.8×1.4-10L and MSOP-10 Packages

APPLICATIONS

Cellular Phones

Digital Cameras

Portable Equipment

Computer Peripherals

Battery-Powered Systems

Routes Signals for USB 2.0 Full-Speed

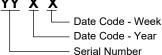
PACKAGE/ORDERING INFORMATION

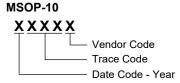
MODEL	PACKAGE DESCRIPTION	SPECIFIED TEMPERATURE RANGE	ORDERING NUMBER	PACKAGE MARKING	PACKING OPTION
SGM7229	UTQFN-1.8×1.4-10L	-40°C to +85°C	SGM7229YUWQ10G/TR	NDXX	Tape and Reel, 3000
	MSOP-10	-40°C to +85°C	SGM7229YMS10G/TR	SGM7229 YMS10 XXXXX	Tape and Reel, 4000

MARKING INFORMATION

NOTE: XX = Date Code. XXXXX = Date Code, Trace Code and Vendor Code.

UTQFN-1.8×1.4-10L YY X X





Green (RoHS & HSF): SG Micro Corp defines "Green" to mean Pb-Free (RoHS compatible) and free of halogen substances. If you have additional comments or questions, please contact your SGMICRO representative directly.

ABSOLUTE MAXIMUM RATINGS

V _{CC} to GND	0V to 6V
Analog, Digital Voltage Range	0.3V to V_{CC} + 0.3V
Continuous Current HSDn or Dn	±50mA
Peak Current HSDn or Dn	±100mA
Junction Temperature	+150°C
Storage Temperature Range	65°C to +150°C
Lead Temperature (Soldering, 10s)	+260°C
ESD Susceptibility	
HBM	2500V
MM	400V
CDM	1000V

RECOMMENDED OPERATING CONDITIONS

Operating Temperature Range-40°C to +85°C

OVERSTRESS CAUTION

Stresses beyond those listed in Absolute Maximum Ratings may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect reliability. Functional operation of the device at any conditions beyond those indicated in the Recommended Operating Conditions section is not implied.

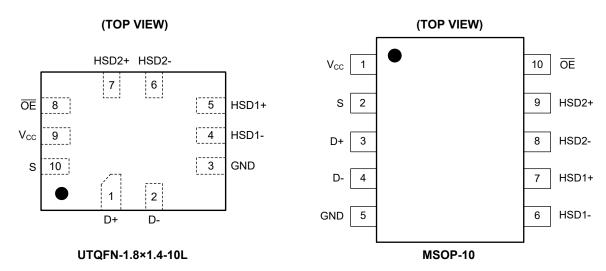
ESD SENSITIVITY CAUTION

This integrated circuit can be damaged if ESD protections are not considered carefully. SGMICRO recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage. ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because even small parametric changes could cause the device not to meet the published specifications.

DISCLAIMER

SG Micro Corp reserves the right to make any change in circuit design, or specifications without prior notice.

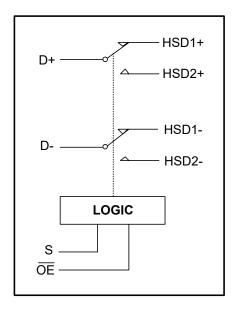
PIN CONFIGURATIONS



PIN DESCRIPTION

PIN		NAME	FUNCTION		
UTQFN-1.8×1.4-10L	MSOP-10	NAME	FUNCTION		
1	3	D+	USB Data Bus.		
2	4	D-	USB Data Bus.		
3	5	GND	Ground.		
4	6	HSD1-	Multiplexed Source Input.		
5	7	HSD1+	Multiplexed Source Input.		
6	8	HSD2-	Multiplexed Source Input.		
7	9	HSD2+	Multiplexed Source Input.		
8	10	ŌĒ	Output Enable Control Pin.		
9	1	V _{CC}	Positive Power Supply Pin.		
10	2	S	Select Input Pin.		

BLOCK DIAGRAM



FUNCTION TABLE

ŌĒ	S	HSD1+, HSD1-	HSD2+, HSD2-
0	0	ON	OFF
0	1	OFF	ON
1	×	OFF	OFF

NOTE: Switches shown for logic "0" input.

ELECTRICAL CHARACTERISTICS

(V_{CC} = 3.3V, Full = -40°C to +85°C, typical values are at T_A = +25°C, unless otherwise noted.)

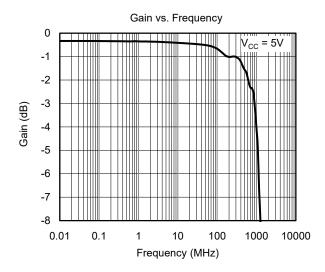
PARAMETER	SYMBOL	CONDITIONS	TEMP	MIN	TYP	MAX	UNITS
ANALOG SWITCH							•
Analog I/O Voltage (HSD1+, HSD1-, HSD2+, HSD2-)	V _{IS}		Full	0		V _{CC}	V
On-Resistance	R _{on}	V_{CC} = 3V, V_{IS} = 0V to 0.4V, I_D = 8mA, Test Circuit 1	+25°C		6	7	Ω
	. 1011		Full			8	32
On-Resistance Match between Channels	ΔR_{ON}	$V_{CC} = 3V$, $V_{IS} = 0V$ to 0.4V,	+25°C		0.2	0.8	Ω
On resistance mater between Gridinies	ZIKON	I _D = 8mA, Test Circuit 1	Full			0.9	
On-Resistance Flatness	R _{FLAT(ON)}	$V_{CC} = 3V$, $V_{IS} = 0V$ to 1V,	+25°C		2	3	Ω
On resistance rightness	· FLAT(ON)	I _D = 8mA, Test Circuit 1	Full			3.5	
Increase in I _{CC} per Control Voltage	I _{CCT}	$V_{CC} = 3.6V$, V_S or $V_{\overline{OE}} = 1.8V$	+25°C		2	3	μA
Therease in the per control voltage	ICCI		Full			3.5	μΑ
Power Off Leakage Current (D+, D-)	I _{OFF}	$V_{CC} = 0V, V_D = 0V \text{ to } 3.6V, V_S, V_{\overline{0E}} = 0V \text{ or } 3.6V $ $V_{CC} = 3.6V, V_{IS} = 3.3V/0.3V,$	Full			0.5	μΑ
Source Off Leakage Current	I _{HSD2(OFF)} , I _{HSD1(OFF)}	$V_D = 0.3V/3.3V$	Full			0.5	μΑ
Channel On Leakage Current	I _{HSD2(ON)} , I _{HSD1(ON)}	$V_{CC} = 3.6V, V_{IS} = 3.3V/0.3V, V_{D} = 3.3V/0.3V \text{ or floating}$	Full			0.5	μA
DIGITAL INPUTS							
Input High Voltage	V _{IH}		Full	1.5			V
Input Low Voltage	V _{IL}		Full			0.4	V
Input Leakage Current	I _{IN}	V_S , $V_{\overline{OE}} = 0V$ or V_{CC}	Full			0.5	μΑ
DYNAMIC CHARACTERISTICS							
Turn-On Time	t _{ON}	$V_{IS} = 0.8V, R_{L} = 50\Omega,$	+25°C		30		ns
Turn-Off Time	t _{OFF}	C _L = 10pF, Test Circuit 2	+25°C		18		ns
Break-Before-Make Time Delay	t _D	$V_{IS} = 0.8V$, $R_L = 50\Omega$, $C_L = 10pF$, Test Circuit 3	+25°C		14		ns
Propagation Delay	t _{PD}	$R_L = 50\Omega, C_L = 10pF$	+25°C		0.5		ns
Off Isolation	O _{ISO}	Signal = 0dBm, R_L = 50 Ω , f = 250MHz, Test Circuit 4	+25°C		-26		dB
Channel-to-Channel Crosstalk	X _{TALK}	Signal = 0dBm, R _L = 50Ω, f = 250MHz, Test Circuit 5	+25°C		-20		dB
-3dB Bandwidth	BW	Signal = 0dBm, R_L = 50 Ω , C_L = 5pF, Test Circuit 6	+25°C		850		MHz
Channel-to-Channel Skew	t _{SKEW}	$R_L = 50\Omega$, $C_L = 10pF$	+25°C		0.5		ns
Charge Injection Select Input to Common I/O	Q	$V_G = GND, C_L = 1nF, R_G = 0\Omega,$ $Q = C_L \times V_{OUT}, Test Circuit 7$	+25°C		2.5		рС
HSD+, HSD-, D+, D- On-Capacitance	C _{ON}	f = 1MHz	+25°C		8		pF

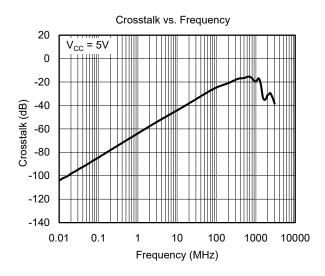
ELECTRICAL CHARACTERISTICS (continued)

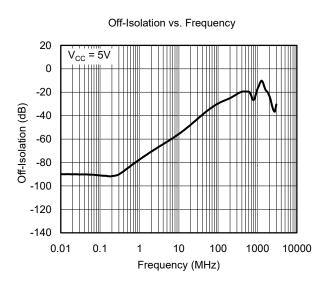
(V_{CC} = 5V, Full = -40°C to +85°C, typical values are at T_A = +25°C, unless otherwise noted.)

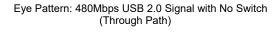
PARAMETER	SYMBOL	CONDITIONS	TEMP	MIN	TYP	MAX	UNITS
ANALOG SWITCH		1				•	•
Analog I/O Voltage (HSD1+, HSD1-, HSD2+, HSD2-)	V _{IS}		Full	0		V _{CC}	V
	Б	$V_{IS} = 0V \text{ to } 0.4V,$	+25°C		4.5	5.5	
On-Resistance	R _{on}	I _D = 8mA, Test Circuit 1	Full			6.5	Ω
On-Resistance Match between Channels	ΔR _{on}	V _{IS} = 0V to 0.4V,	+25°C		0.2	0.8	Ω
On-resistance match between channels	ΔΙΝΟΝ	I _D = 8mA, Test Circuit 1	Full			0.9	22
On-Resistance Flatness	R _{FLAT(ON)}	$V_{IS} = 0V \text{ to } 1V,$	+25°C		0.5	0.75	Ω
On-resistance riadiess	FLAT(ON)	I _D = 8mA, Test Circuit 1	Full			0.9	32
Increase in I _{CC} per Control Voltage	I _{CCT}	$V_{CC} = 5.5V$, V_S or $V_{\overline{OE}} = 1.8V$	+25°C		14	18	ΠΔ
microase in ice per control voltage	icei		Full			22	μA
Power Off Leakage Current (D+, D-)	I _{OFF}	$V_{CC} = 0V, V_D = 0V \text{ to } 5.5V, V_S, V_{\overline{OE}} = 0V \text{ or } 5.5V$	Full			0.5	μA
Source Off Leakage Current	I _{HSD2(OFF)} , I _{HSD1(OFF)}	$V_{CC} = 5.5V, V_{IS} = 4.5V/1V,$ $V_{D} = 1V/4.5V$	Full			0.5	μA
Channel On Leakage Current	I _{HSD2(ON)} ,	$V_{CC} = 5.5V, V_{IS} = 4.5V/1V,$ $V_{D} = 4.5V/1V$ or floating	Full			0.5	μA
DIGITAL INPUTS		<u> </u>					
Input High Voltage	V _{IH}	V _{CC} = 5.5V	Full	1.8			V
Input Low Voltage	V _{IL}	V _{CC} = 5.5V	Full			0.6	V
Input Leakage Current	I _{IN}	$V_{CC} = 5.5V$, V_{S} , $V_{\overline{OE}} = 0V$ or V_{CC}	Full			0.5	μA
DYNAMIC CHARACTERISTICS							
Turn-On Time	t _{ON}	$V_{IS} = 0.8V, R_{L} = 50\Omega,$	+25°C		22		ns
Turn-Off Time	t _{OFF}	C _L = 10pF, Test Circuit 2	+25°C		14		ns
Break-Before-Make Time Delay	t _D	$V_{IS} = 0.8V$, $R_L = 50\Omega$, $C_L = 10pF$, Test Circuit 3	+25°C		9		ns
Propagation Delay	t _{PD}	$R_L = 50\Omega, C_L = 10pF$	+25°C		0.5		ns
Off Isolation	O _{ISO}	Signal = 0dBm, R_L = 50 Ω , f = 250MHz, Test Circuit 4	+25°C		-26		dB
Channel-to-Channel Crosstalk	X _{TALK}	Signal = 0dBm, R_L = 50 Ω , f = 250MHz, Test Circuit 5	+25°C		-20		dB
-3dB Bandwidth	BW	Signal = 0dBm, R_L = 50 Ω , C_L = 5pF, Test Circuit 6	+25°C		850		MHz
Channel-to-Channel Skew	t _{SKEW}	$R_L = 50\Omega, C_L = 10pF$	+25°C		0.5		ns
Charge Injection Select Input to Common I/O	Q	$V_G = GND, C_L = 1nF, R_G = 0\Omega,$ $Q = C_L \times V_{OUT}, Test Circuit 7$	+25°C		3.5		pC
HSD+, HSD-, D+, D- On-Capacitance	C _{ON}	f = 1MHz	+25°C		8		pF
POWER REQUIREMENTS	•				•	•	•
Power Supply Range	V _{CC}		Full	1.8		5.5	V
Power Supply Current	Icc	$V_{CC} = 5.5V$, V_{S} , $V_{\overline{OE}} = 0V$ or V_{CC}	Full			0.5	μΑ

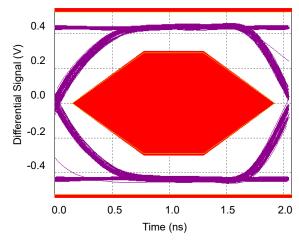
TYPICAL PERFORMANCE CHARACTERISTICS

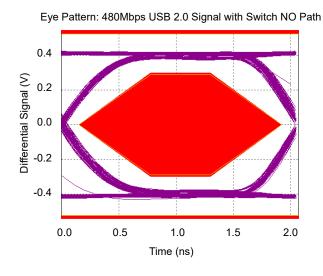




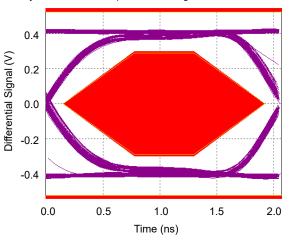




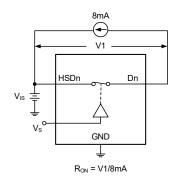




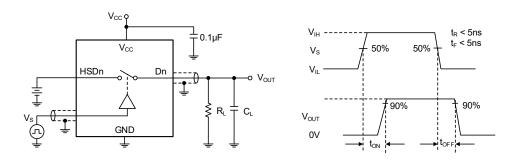




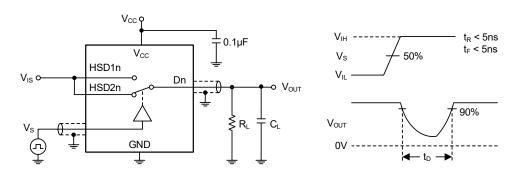
TEST CIRCUITS



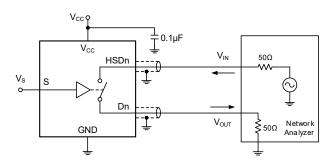
Test Circuit 1. On-Resistance



Test Circuit 2. Switching Times (t_{ON} , t_{OFF})

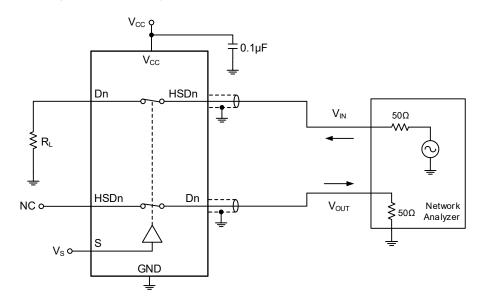


Test Circuit 3. Break-Before-Make Time Delay (t_D)



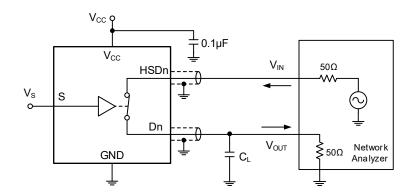
Test Circuit 4. Off Isolation

TEST CIRCUITS (continued)

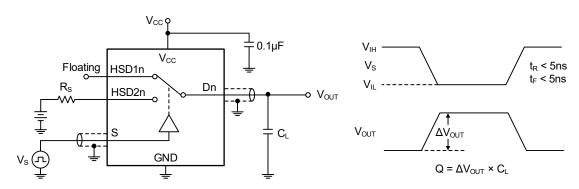


Channel-to-Channel Crosstalk = -20 log (V_{HSDn}/V_{OUT})

Test Circuit 5. Channel-to-Channel Crosstalk



Test Circuit 6. -3dB Bandwidth



Test Circuit 7. Charge Injection (Q)

APPLICATION NOTES

Meeting USB 2.0 V_{BUS} Short Requirements Power-Off Protection

When D+ or D- is shorted to V_{BUS} , there is a special protection circuit inside the SGM7229, so that the device will not be damaged within 24 hours. In case of power-down or over-voltage event, the protection circuit can prevent the leakage signal on D+/D- pins to ensure the reliability of the system.

Power-On Protection

The USB 2.0 specification requires USB device to ensure that the device will not be damaged even if V_{BUS} short-circuit occurs during data transmission. Therefore, under over-voltage conditions, the SGM7229 will limit the current flowing back to the V_{CC} track, and the current will not exceed the safe operating range.

REVISION HISTORY

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

December 2021 – REV.A to REV.B	Page
Updated Electrical Characteristics section	5, 6
Changes from Original (DECEMBER 2018) to REV.A	
Changed from product preview to production data	All

